

MN74HC02/MN74HC02S

Quad 2-Input NOR Gates

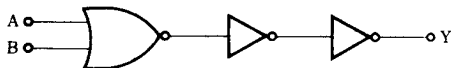
Description

MN74HC02/MN74HC02S contain four 2-input isolation NOR gate circuits.

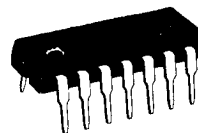
Adoption of a silicon gate CMOS process has resulted in low power dissipation, a high noise margin equivalent to a standard CMOS, and an operation speed of LS TTL. Input/output transfer characteristics have been improved by applying a buffer to the gate output, and fluctuation of transfer time due to increased load capacitance is limited to the minimum. LS TTL 10-inputs can be directly driven.

Resistors and diodes are provided in V_{DD} and V_{SS} for protection of the input/output against damage by static electricity. Same pin configuration and function as the standard 54LS/74LS logic family.

Logic diagram (1 gate)



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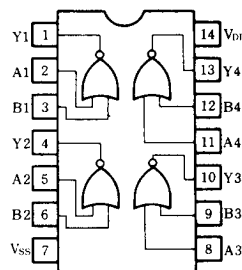
14-pin plastic DIL package

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14-pin Panaflat package (SO-14D)

Pin configuration (top view)



Absolute maximum ratings

■ Absolute maximum ratings					
Item			Sym.	Rating	Unit
Supply voltage			V _{DD}	−0.5~7.0	V
Input/output voltage			V _I , V _O	−0.5~V _{DD} +0.5	V
Input current			I _I	±20	mA
Output current			I _O	±25	mA
Power dissipation	MN74HC02	T _a = −40~+60℃	P _D	400	mW
		T _a = +60~+85℃		Decrease to 200mW at the rate of 8mW/℃	
	MN74HC02S	T _a = −40~+60℃	P _D	275	mW
		T _a = +60~+85℃		Decrease to 200mW at the rate of 3.8mW/℃	
Storage temperature range			T _{stg}	−65~+150	℃
Supply current			I _{DD} , I _{SS}	±50	mA

■ Recommended operating conditions

Item	Sym.	Rating	Unit
Operating supply voltage	V_{DD}	1.4 ~ 6.0	V
Input voltage	V_I	0 ~ V_{DD}	V
Operating temperature range	T_{opr}	-40 ~ +85	°C
Input rise and fall time	t_r, t_f	0 ~ 500	ns

■ DC characteristics ($V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$)

Item	Sym.	Test conditions	$T_a = -40^\circ\text{C}$		$T_a = +25^\circ\text{C}$		$T_a = +85^\circ\text{C}$		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
Quiescent supply current	I_{DD}	$V_I = V_{DD}$ or V_{SS}		2		2		20	μA
High level input voltage	V_{IH}	$V_O = 0.5V$ $ I_O \leq 1\mu\text{A}$	$V_{DD} = 4.5V$	3.15		3.15		3.15	V
			$V_{DD} = 5.0V$	3.50		3.50		3.50	
			$V_{DD} = 5.5V$	3.85		3.85		3.85	
Low level input voltage	V_{IL}	$V_O = V_{DD} - 1.0V$ $ I_O \leq 1\mu\text{A}$	$V_{DD} = 4.5V$		0.9		0.9		V
			$V_{DD} = 5.0V$		1.0		1.0		
			$V_{DD} = 5.5V$		1.1		1.1		
Input current	$\pm I_I$	$V_I = V_{DD}$ or V_{SS}		0.3		0.3		1	μA
High level output voltage	V_{OH}	$V_I = V_{SS}$, $ I_O \leq 1\mu\text{A}$	$V_{DD} - 0.05$		$V_{DD} - 0.05$		$V_{DD} - 0.05$		V
Low level output voltage	V_{OL}	$V_I = V_{DD}$ or V_{SS} , $ I_O \leq 1\mu\text{A}$		0.05		0.05		0.05	V
High level output current	I_{OH}	$V_I = V_{SS}$, $V_O = V_{IL} - 0.8V$	-6		-5		-4		mA
Low level output current	I_{OL}	$V_I = V_{DD}$ or V_{SS} , $V_O = 0.4V$	6		5		4		mA

■ AC characteristics ($V_{DD} = 5V$, $V_{SS} = 0V$, $T_a = 25^\circ\text{C}$ Input transition time $\leq 6\text{ns}$, $C_L = 50\text{pF}$)

Item	Sym.	Test conditions	Min.	Typ.	Max.	Unit
Output rise time	t_{TLH}			8	15	ns
Output fall time	t_{THL}			6	15	ns
Propagation time (L→H)	t_{PLH}			8	15	ns
Propagation time (H→L)	t_{PHL}			8	15	ns

※ AC characteristics measurement waveform

